



### **40V P-Channel Enhancement Mode MOSFET**

Voltage

-40 V

Current

-44 A

#### **Features**

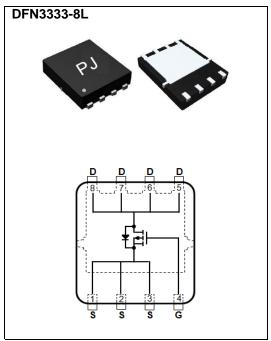
- $R_{DS(ON)}$ ,  $V_{GS}@-10V$ ,  $I_D@-10A<17m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-8A<25m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.001 ounces, 0.03 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	-40	\	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	I <sub>D</sub>	-44	А	
	T <sub>C</sub> =100°C		-28		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	-135		
Power Dissipation	T <sub>C</sub> =25°C	Po	59.5	14/	
	T <sub>C</sub> =100°C		24	W	
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	-8.5		
	T <sub>A</sub> =70°C		-7	Α	
Power Dissipation	T <sub>A</sub> =25°C	Б	2	10/	
	T <sub>A</sub> =70°C	Pb	1.3	W	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	လ	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2.1	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$		-1	-1.6	-2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-10A	-	14	17	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-8A	-	20	25	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V	-	_	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)		<del>,</del>				
Total Gate Charge	$Q_g$	$V_{DS}$ =-32V, $I_{D}$ =-10A, $V_{GS}$ =-4.5V (Note 1,2)	-	19	-	nC
Gate-Source Charge	$Q_gs$		-	5.3	-	
Gate-Drain Charge	$Q_{gd}$		-	6.6	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHZ	-	2030	-	pF ns
Output Capacitance	Coss		-	190	-	
Reverse Transfer Capacitance	Crss	I= IIVII IZ	-	139	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	8.6	-	
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =-20V, $I_{D}$ =-1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	9.6	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	77	-	
Turn-Off Fall Time	t <sub>f</sub>		-	39	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,				-44	Α
Diode Forward Current	I <sub>S</sub>		-	-	-44	^
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.7	-1	V

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

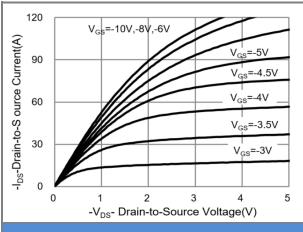


Fig.1 On-Region Characteristics

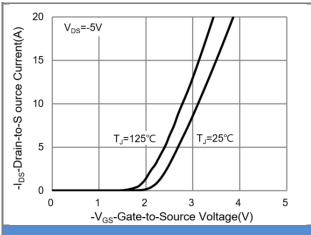


Fig.2 Transfer Characteristics

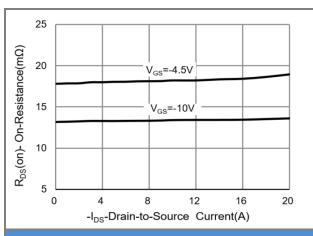


Fig.3 On-Resistance vs. Drain Current

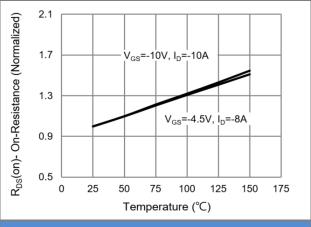


Fig.4 On-Resistance vs. Junction temperature

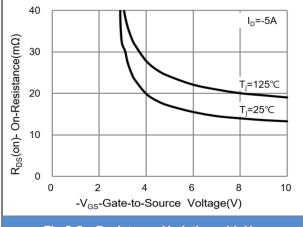


Fig.5 On-Resistance Variation with V<sub>GS</sub>

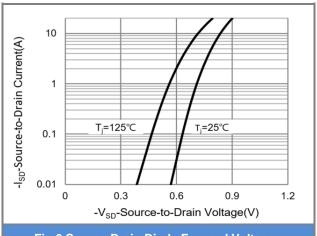


Fig.6 Source-Drain Diode Forward Voltage





#### TYPICAL CHARACTERISTIC CURVES

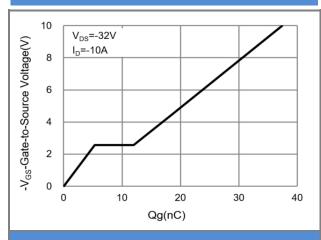


Fig.7 Gate-Charge Characteristics

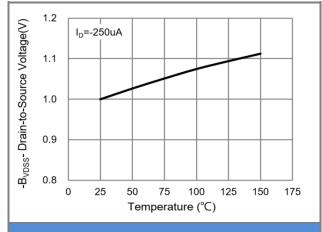


Fig.8 Breakdown Voltage Variation vs. Temperature

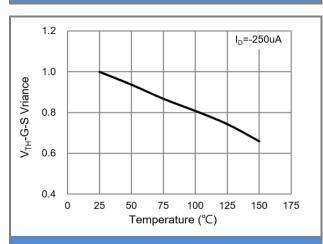


Fig.9 Threshold Voltage Variation with Temperature

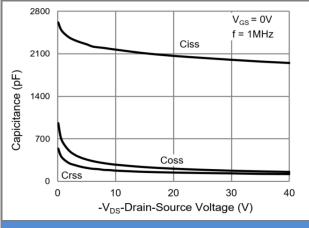


Fig.10 Capacitance vs. Drain-Source Voltage

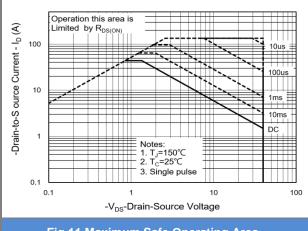


Fig.11 Maximum Safe Operating Area

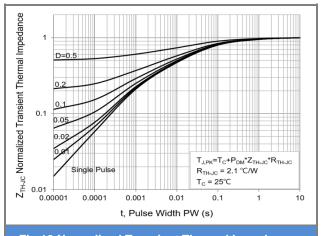


Fig.12 Normalized Transient Thermal Impedance

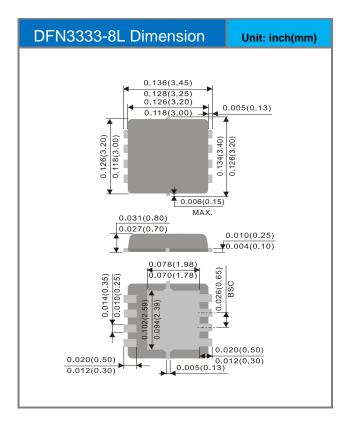


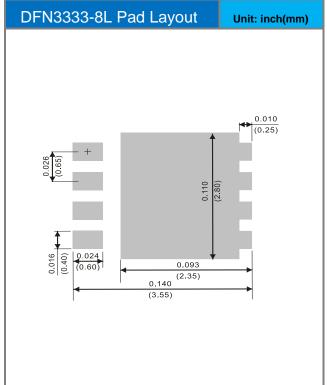


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4441P-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4441	Halogen free

### **Packaging Information & Mounting Pad Layout**









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